

**IN THE CLAIMS:**

Please amend claims 6, 8, 9 and 10.

6. (currently amended) A method of forming a copper interconnect, comprising:  
forming a barrier layer over a substrate having at least one trench therein;  
forming a copper seed layer on the surface of the barrier layer;  
forming a copper layer over the barrier and seed layers;  
removing a portion of the copper layer by chemical mechanical polishing with a first slurry comprising a chelating organic acid buffer system, colloidal silica, and a low electrochemical oxidizer; and  
removing at least a portion of the barrier layer by chemical mechanical polishing with a second slurry comprising a chelating organic acid buffer system, and colloidal silica[;], wherein the second slurry is formed without the oxidizer.
7. (original) The method of Claim 6, wherein the barrier layer comprises tantalum.
8. (currently amended) The method of Claim [[7,]] 6, wherein the chelating organic acid buffer system comprises citric acid and potassium citrate.
9. (currently amended) The method of Claim [[8,]] 6, wherein the oxidizer comprises hydrogen peroxide.
10. (currently amended) The method of Claim [[9,]] 6, wherein the first slurry further comprises a corrosion inhibitor.
11. (original) The method of Claim 10, wherein the first slurry has a pH in the range of 3 to 6, and the corrosion inhibitor comprises benzotriazole.